

TOSHIBA PHOTOCOUPLER GaAlAs IRED & PHOTO-IC

TLP112A

DIGITAL LOGIC ISOLATION

LINE RECEIVER

POWER SUPPLY CONTROL FEEDBACK CONTROL

SWITCHING POWER SUPPLY

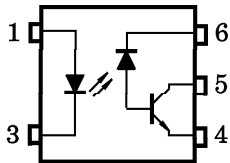
TRANSISTOR INVERTOR

The TOSHIBA MINI FLAT COUPLER TLP112A is a small outline coupler, suitable for surface mount assembly.

TLP112A consists of a high output power GaAlAs light emitting diode, optically coupled to a high speed detector of one chip photodiode-transistor.

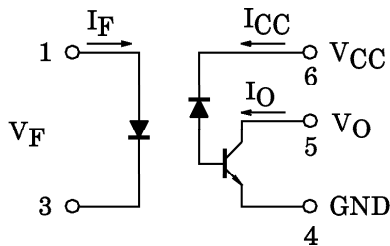
- Isolation Voltage : 2500Vrms (Min.)
- Switching Speed : $t_{pHL} = 0.8\mu s$, $t_{pLH} = 0.8\mu s$ (Max.) ($R_L = 1.9k\Omega$)
- TTL Compatible
- UL Recognized : UL1577, File No. E67349

PIN CONFIGURATION (TOP VIEW)

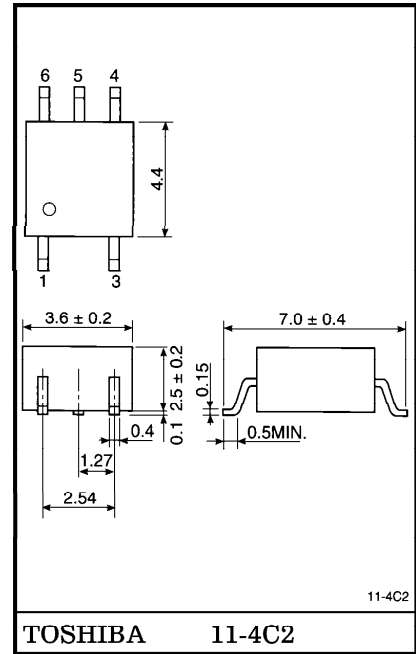


- 1 : ANODE
- 3 : CATHODE
- 4 : EMITTER (GND)
- 5 : COLLECTOR (OUTPUT)
- 6 : VCC

SCHEMATIC



Unit in mm



Weight : 0.09g

961001EBC2

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MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
LED	Forward Current (Note 1)	I _F	20	mA
	Pulse Forward Current (Note 2)	I _{FP}	40	mA
	Peak Transient Forward Current (Note 3)	I _{FPT}	1	A
	Reverse Voltage	V _R	5	V
DETECTOR	Output Current	I _O	8	mA
	Peak Output Current	I _{OP}	16	mA
	Supply Voltage	V _{CC}	-0.5~15	V
	Output Voltage	V _O	-0.5~15	V
	Output Power Dissipation (Note 4)	P _o	100	mW
Operating Temperature Range		T _{opr}	-55~100	°C
Storage Temperature Range		T _{stg}	-55~125	°C
Lead Soldering Temperature (10s)		T _{sol}	260	°C
Isolation Voltage (AC, 1 min., R.H. ≤ 60%, Note 5)		BVS	2500	V _{rms}

(Note 1) Derate 0.36mA/°C above 70°C.

(Note 2) 50% duty cycle, 1ms pulse width.
Derate 0.72mA/°C above 70°C.

(Note 3) Pulse width ≤ 1μs, 300pps.

(Note 4) Derate 1.8mW/°C above 70°C.

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	V _F	I _F = 16mA	1.22	1.42	1.72	V
	Forward Voltage Temperature Coefficient	ΔV _F /ΔTa	I _F = 16mA	—	-2	—	mV/°C
	Reverse Current	I _R	V _R = 3V	—	—	10	μA
	Capacitance Between Terminals	C _T	V _F = 0, f = 1MHz	—	30	—	pF
DETECTOR	High Level Output Current	I _{OH} (1)	I _F = 0mA, V _{CC} = V _O = 5.5V	—	3	500	nA
		I _{OH} (2)	I _F = 0mA, V _{CC} = V _O = 15V	—	—	5	μA
		I _{OH}	I _F = 0mA, V _{CC} = V _O = 15V Ta = 70°C	—	—	50	
	High Level Supply Current	I _{CC} H	I _F = 0mA, V _{CC} = 15V	—	0.01	1	μA
COUPLED	Current Transfer Ratio	I _O / I _F	I _F = 16mA, V _{CC} = 4.5V V _O = 0.4V	20	—	—	%
	Low Level Output Voltage	V _{OL}	I _F = 16mA, V _{CC} = 4.5V I _O = 2.4mA	—	—	0.4	V
	Isolation Resistance	R _S	R.H. ≤ 60% V _S = 500V DC (Note 5)	5 × 10 ¹⁰	10 ¹⁴	—	Ω
	Stray Capacitance Between Input to Output	C _S	V _S = 0, f = 1MHz (Note 5)	—	0.8	—	pF

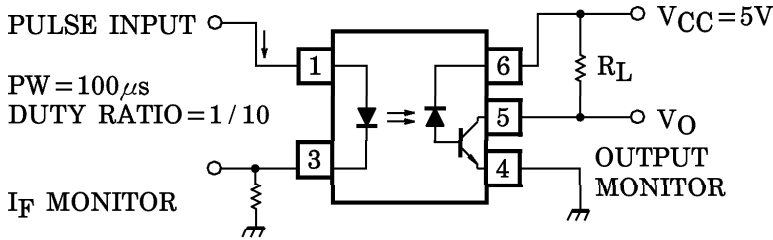
SWITCHING CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CIR-CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Propagation Delay Time (H→L)	t _{pHL}	1	I _F = 0→16mA V _{CC} = 5V, R _L = 1.9kΩ	—	—	0.8	μs
Propagation Delay Time (L→H)	t _{pLH}	1	I _F = 16→0mA V _{CC} = 5V, R _L = 1.9kΩ	—	—	0.8	μs
Common Mode Transient Immunity at High Output Level	CM _H	2	I _F = 0mA, V _{CM} = 200V _{p-p} R _L = 4.1kΩ	—	1500	—	V / μs
Common Mode Transient Immunity at Low Output Level	CM _L	2	I _F = 16mA, V _{CM} = 200V _{p-p} R _L = 4.1kΩ	—	-1500	—	V / μs

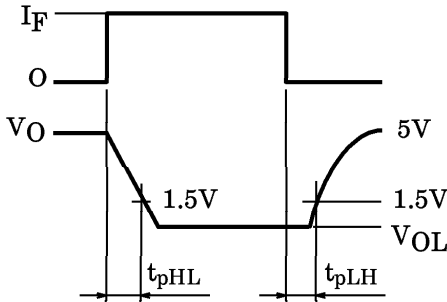
(Note 5) Device considered a two-terminal device : Pins 1 and 3 shorted together and Pin 4, 5 and 6 shorted together.

(Note 6) Maximum electrostatic discharge voltage for any pins : 100V (C=200pF, R=0)

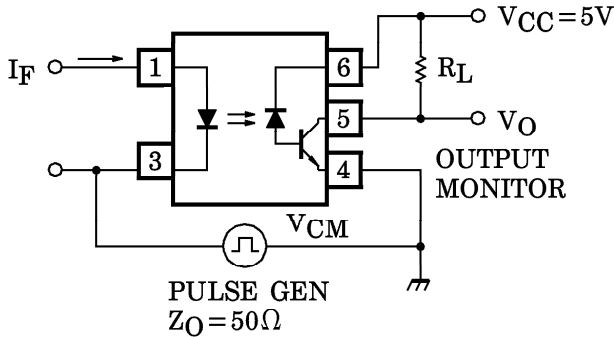
TEST CIRCUIT 1 : Switching Time Test Circuit



PW = 100 μs
DUTY RATIO = 1 / 10



TEST CIRCUIT 2 : Common Mode Transient Immunity Test Circuit



$$CM_H = \frac{160 (V)}{t_r (\mu s)}, \quad CM_L = \frac{160 (V)}{t_f (\mu s)}$$

